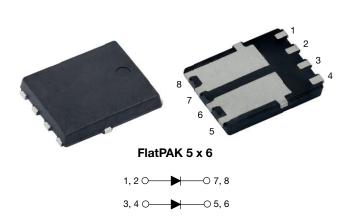
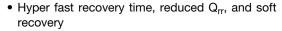
# Hyper Fast Rectifier, 2 x 4 A FRED Pt®



PRODUCT SUMMARY							
Package	FlatPAK 5 x 6						
I <sub>F(AV)</sub>	2 x 4 A						
$V_{R}$	200 V						
V <sub>F</sub> at I <sub>F</sub>	0.7 V						
t <sub>rr (typ.)</sub>	25 ns						
T <sub>J</sub> max.	175 °C						
Diode variation	Separated cathode						

#### **FEATURES**





• 175 °C maximum operating junction temperature

175 O maximum operating junction temperature

COMPLIANT HALOGEN FREE

Specific for output and snubber operation

- Low forward voltage drop
- Low leakage current
- Meets MSL level 1 per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912">www.vishav.com/doc?99912</a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyper fast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyper fast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

#### **MECHANICAL DATA**

Case: FlatPAK 5 x 6

Molding compound meets UL 94 V-0 flamming rating Base P/N-M3 - halogen-free, RoHS-compliant

Terminals: matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

M3 suffix meets JESD 201 class 2 whisker test

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage		V <sub>RRM</sub>		200	V			
Average rectified forward current per	per device		T <sub>Solderpad</sub> = 170 °C, DC	8	A			
	per device	I <sub>F(AV)</sub>	T <sub>Solderpad</sub> = 169 °C, D = 0.5	0				
Non-repetitive peak surge current -	per device		T 05 °C 10 ma sinussidal mulas	173	A			
	per diode	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C, 10 ms sinusoidal pulse	87				
Operating junction and storage temperatures		T <sub>J</sub> , T <sub>Stg</sub>		-55 to +175	°C			



<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS MIN. TYP. MA				UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	200	-	-			
Forward voltage, per diode	V <sub>F</sub>	$I_F = 4 A$	-	0.87	0.96	V		
		I <sub>F</sub> = 4 A, T <sub>J</sub> = 150 °C	-	0.7	0.78			
Devenue legicone everent nor die de	I <sub>R</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	-	2			
Reverse leakage current, per diode		$T_J = 150  ^{\circ}\text{C},  V_R = V_R  \text{rated}$	-	7	80	- μΑ		
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 200 V	-	19	-	pF		

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
		I <sub>F</sub> = 1.0 A, dI <sub>F</sub> /dt =	= 50 A/μs, V <sub>R</sub> = 30 V	-	20	-			
Reverse recovery time		I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1 A, I <sub>rr</sub> = 0.25 A		-	-	25	no		
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	17	-	ns		
		T <sub>J</sub> = 125 °C		-	29	-			
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	$I_F = 4 A$ $dI_F/dt = 200 A/\mu s$ $V_R = 160 V$	-	2.1	-	Α		
		T <sub>J</sub> = 125 °C		-	4	-	A		
Reverse recovery charge	0	T <sub>J</sub> = 25 °C		-	18	-	200		
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	60	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNIT									
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-55	-	175	°C			
Thermal resistance, junction to ambient, per diode	R <sub>thJA</sub> (1)(2)		-	89	103	°C/W			
Thermal resistance, junction to case, per diode	R <sub>thJC</sub> (3)		-	1.8	2.1	C/VV			

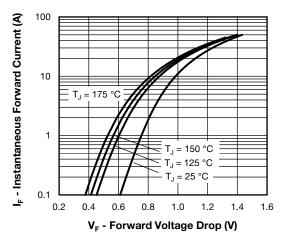
### Notes

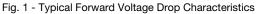
 $<sup>^{(1)}</sup>$  The heat generated must be less than the thermal conductivity from junction to ambient:  $dP_D/dT_J < 1/R_{thJA}$ 

<sup>(2)</sup> Free air, mounted or recommended copper pad area; thermal resistance R<sub>thJA</sub> - junction to ambient

<sup>(3)</sup> Mounted on infinite heatsink







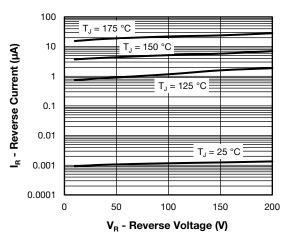


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

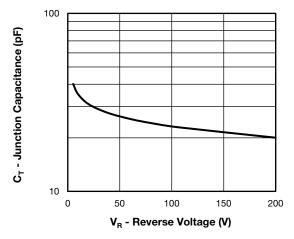


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

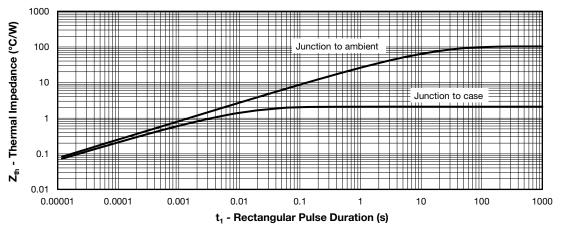


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

#### www.vishay.com

## Vishay Semiconductors

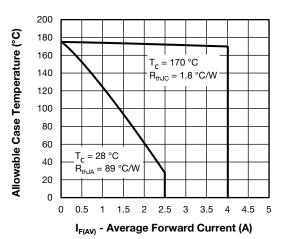
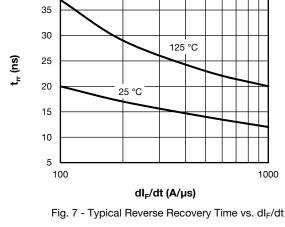


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current



40

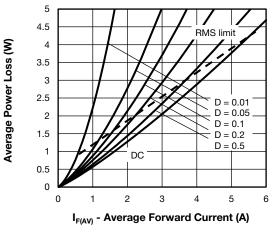


Fig. 6 - Forward Power Loss Characteristics

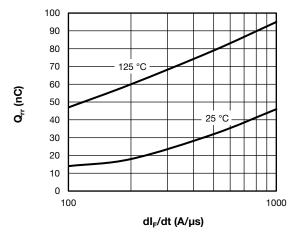
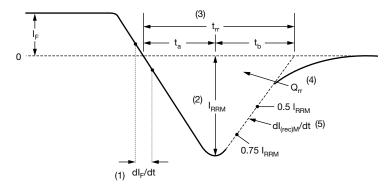


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt



- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75  $I_{\text{RRM}}$  and 0.50  $I_{\text{RRM}}$ extrapolated to zero current.
- (4) Q<sub>rr</sub> area under curve defined by t<sub>rr</sub> and I<sub>RRM</sub>

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

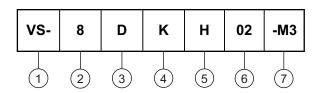
(5)  $dI_{(rec)M}/dt$  - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 9 - Reverse Recovery Waveform and Definitions



### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current rating (8 = 8 A)

**3** - Circuit configuration:

D = separated cathode

4 - K = FlatPAK package

Process type,

H = hyper fast recovery

6 - Voltage code (02 = 200 V)

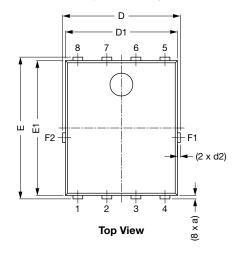
8 - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

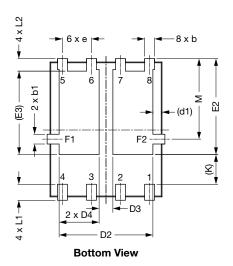
ORDERING INFORMATION (example)									
PREFERRED P/N UNIT WEIGHT (g) PREFERRED PACKAGE CODE BASE QUANTITY PACKAGING DESCRIPTION									
VS-8DKH02-M3/H	0.10	Н	1500	7"diameter plastic tape and reel					
VS-8DKH02-M3/I	0.10	I	6000	13"diameter plastic tape and reel					

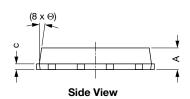
LINKS TO RELATED DOCUMENTS						
Dimensions <u>www.vishay.com/doc?96056</u>						
Part marking information	www.vishay.com/doc?96059					
Packaging information	www.vishay.com/doc?88869					

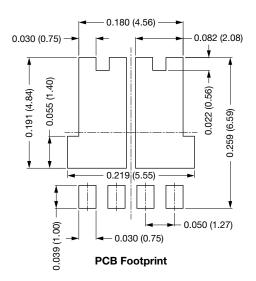
# FlatPAK 5 x 6 (Dual)

### **DIMENSIONS** in inches (millimeters)









DIM		INCHES			MILLIMETERS	
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	0.035	0.039	0.043	0.89	0.99	1.09
(a)	-	0.006	-	-	0.15	-
b	0.013	0.017	0.020	0.32	0.43	0.52
b1	0.013	0.017	0.020	0.32	0.43	0.52
С	0.008	-	0.014	0.20	-	0.35
D	0.197	0.203	0.209	5.00	5.15	5.30
D1	0.189	0.193	0.197	4.80	4.90	5.00
D2	0.154	0.161	0.169	3.90	4.10	4.30
D3	0.020	0.024	0.031	0.50	0.60	0.80
D4	0.063	0.069	0.075	1.60	1.75	1.90
(d1)	-	0.016	-	=	0.40	=
(d2)	-	0.005	-	-	0.125	-
Е	0.238	0.244	0.250	6.05	6.20	6.35



## **Outline Dimensions**

### www.vishay.com

# Vishay Semiconductors

DIM.		INCHES			MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.		
E1	0.228	0.232	0.236	5.80	5.90	6.00		
E2	0.157	0.165	0.173	4.00	4.20	4.40		
(E3)	-	0.144	=	-	3.65	=		
е		0.050 BSC			1.27 BSC			
(K)	0.039	-	-	1.00	-	-		
L1	0.019	-	0.043	0.48	-	1.10		
L2	0.012	-	0.031	0.30	-	0.80		
M	0.128	0.138	0.148	3.25	3.50	3.75		
Θ	0°	-	10°	0°	-	10°		

#### Notes

- Dimensioning and tolerancing per ASME Y14.5-2009
- Dimensions D1 and E1 do not include mold flash or gate burrs
- Dimension (XX) means reference only



### **Legal Disclaimer Notice**

Vishay

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.